

CMOS QUAD BUFFER-DRIVER

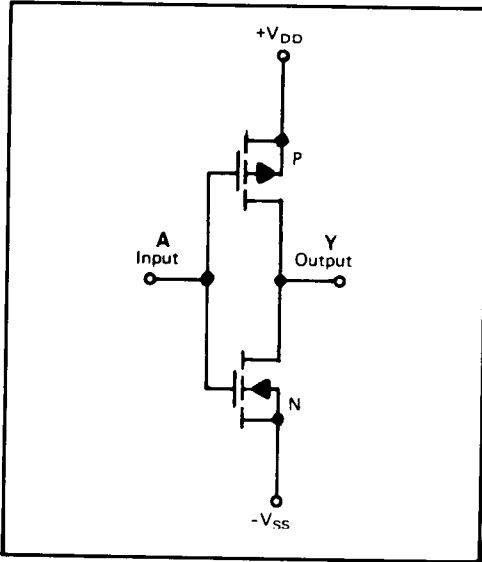
FEATURES

- ◆ Symmetrical High-Current Outputs
- ◆ High-Speed Operation with Large Capacitive Loads
- ◆ Low Output Impedance
- ◆ Diode Protection on all Inputs

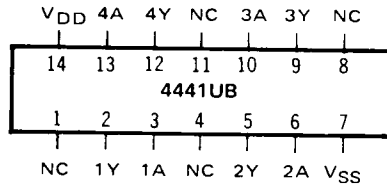
DESCRIPTION

The 4441UB is a monolithic N-channel and P-channel enhancement-mode integrated circuit consisting of four large buffers for very high current capability. This device is useful as a line driver, low-power resistor-network driver for A/D and D/A conversion, display and clock drivers.

SCHEMATIC DIAGRAM (one of four buffers)



CONNECTION DIAGRAM (all packages)



Add suffix for package:

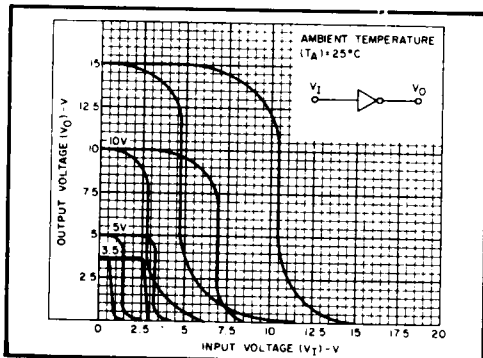
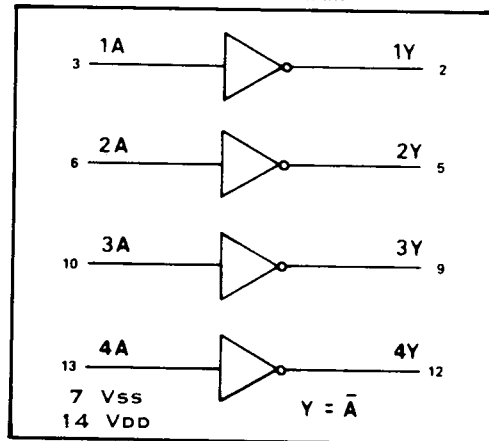
- | | | | |
|---|----------------|---|-------------|
| C | 14-pin Cerdip | F | 14-pin Flat |
| D | 14-pin Ceramic | H | Chip |
| E | 14-pin Epoxy | | |

RECOMMENDED OPERATING CONDITIONS

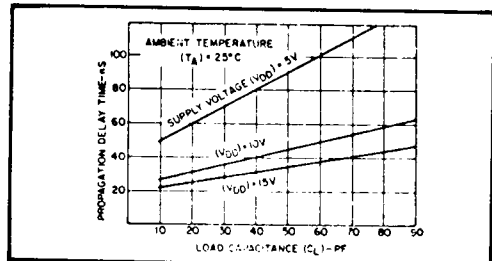
For maximum reliability:

- | | | | |
|-----------------------|-------------------|-------------|-----|
| DC Supply Voltage | $V_{DD} - V_{SS}$ | 3 to 15 | Vdc |
| Operating Temperature | T_A | | |
| C, D, F, H Device | | -55 to +125 | °C |
| E Device | | -40 to +85 | °C |

LOGIC DIAGRAM



Minimum and maximum transfer characteristics.



Typical propagation delay time vs. C_L

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS¹

PARAMETER	V _{DD} (Vdc)	CONDITIONS	T _{LOW} ²		+25°C			T _{HIGH} ²		Units
			Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
QUIESCENT DEVICE CURRENT	I _{DD}	V _{IN} = V _{SS} or V _{DD} All valid input combinations	-	1.0	-	0.005	1.0	-	30	μAdc
			-	2.0	-	0.01	2.0	-	60	
			-	4.0	-	0.02	4.0	-	120	
OUTPUT HIGH (SOURCE) CURRENT	I _{OH}	V _{OH} = 4.6V V _{OH} = 9.5V V _{OH} = 13.5V V _{IN} = V _{SS}	-2.5	-	-2.0	-4.5	-	-1.4	-	mAdc
			-7.3	-	-5.8	-14.0	-	-4.0	-	
			-23.1	-	-18.5	-45	-	-13.0	-	
OUTPUT LOW (SINK) CURRENT	I _{OL}	V _{OL} = 0.4V V _{OL} = 0.5V V _{OL} = 1.5V V _{IN} = V _{DD}	2.4	-	2.4	4.5	-	1.7	-	mAdc
			7.0	-	7.0	14.0	-	4.9	-	
			22.2	-	27	45	-	19	-	

NOTES: ¹ Remaining Static Electrical Characteristics are listed under "4000B Series Family Specifications".

² T_{LOW} = -55°C for C, D, F, H device.

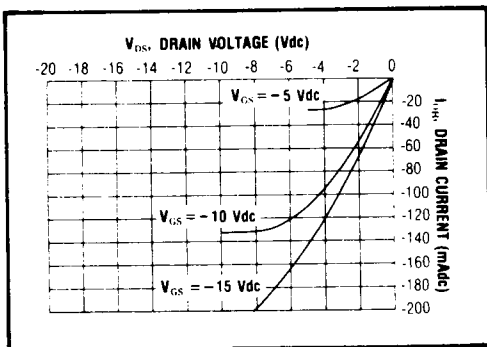
= -40°C for E device.

T_{HIGH} = +125°C for C, D, F, H device.

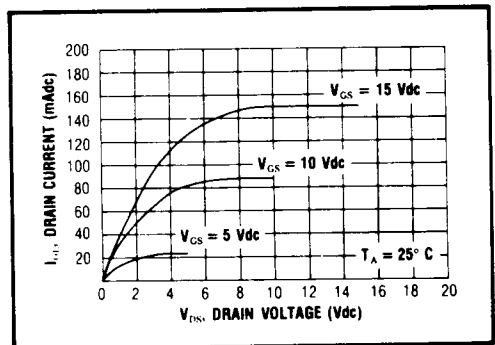
= + 85°C for E device.

DYNAMIC CHARACTERISTICS (C_L = 50pF, T_A = 25°C)

PARAMETER		V _{DD} (Vdc)	Min.	Typ.	Max.	Units
PROPAGATION DELAY TIME	t _{PLH} , t _{PHL}	5	-	90	180	ns
		10	-	45	90	
		15	-	35	70	
OUTPUT TRANSITION TIME	t _{TLH} , t _{THL}	5	-	90	180	ns
		10	-	45	90	
		15	-	35	70	



Typical P-Channel Source Current Characteristics



Typical N-Channel Sink Current Characteristics